

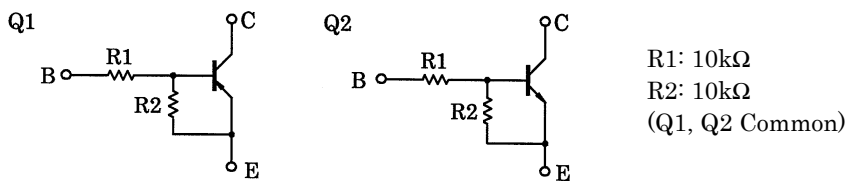
TOSHIBA Transistor
Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

RN4902

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- Including two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit and Bias Resister Values



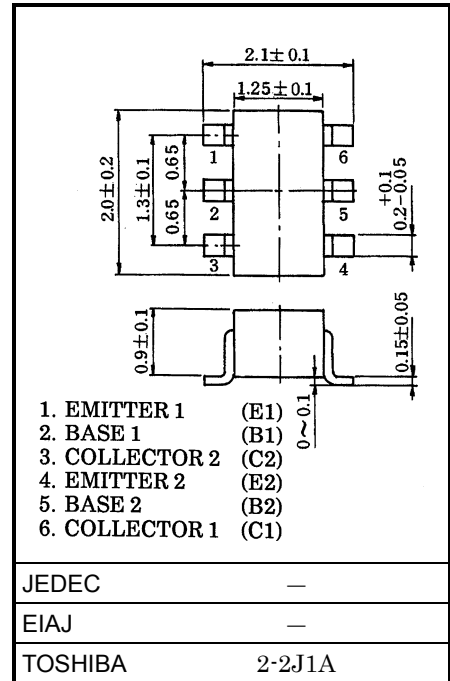
Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-10	V
Collector current	I _C	-100	mA

Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	10	V
Collector current	I _C	100	mA

Unit in mm



Weight: 6.8mg

961001EAA2

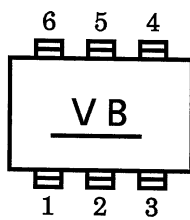
● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

Q1, Q2 Common Maximum Ratings (Ta = 25°C)

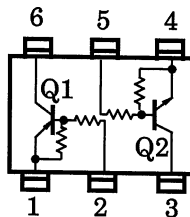
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P_C *	200	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

* Total rating

Marking



Equivalent Circuit (Top View)



961001EAA2'

- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I _{CBO}	—	V _{CB} = -50V, I _E = 0	—	—	-100	nA
	I _{CEO}	—	V _{CE} = -50V, I _B = 0	—	—	-500	
Emitter cut-off current	I _{EBO}	—	V _{EB} = -10V, I _C = 0	-0.38	—	-0.71	mA
DC current gain	h _{FE}	—	V _{CE} = -5V, I _C = -10mA	50	—	—	—
Collector-emitter saturation voltage	V _{CE (sat)}	—	I _C = -5mA, I _B = -0.25mA	—	-0.1	-0.3	V
Input voltage (ON)	V _{I (ON)}	—	V _{CE} = -0.2V, I _C = -5mA	-1.2	—	-2.4	V
Input voltage (OFF)	V _{I (OFF)}	—	V _{CE} = -5V, I _C = -0.1mA	-1.0	—	-1.5	V
Transition frequency	f _T	—	V _{CE} = -10V, I _C = -5mA	—	200	—	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = -10V, I _E = 0, f = 1MHz	—	3	6	pF

Q2 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I _{CBO}	—	V _{CB} = 50V, I _E = 0	—	—	100	nA
	I _{CEO}	—	V _{CE} = 50V, I _B = 0	—	—	500	
Emitter cut-off current	I _{EBO}	—	V _{EB} = 10V, I _C = 0	0.38	—	0.71	mA
DC current gain	h _{FE}	—	V _{CE} = 5V, I _C = 10mA	50	—	—	—
Collector-emitter saturation voltage	V _{CE (sat)}	—	I _C = 5mA, I _B = 0.25mA	—	0.1	0.3	V
Input voltage (ON)	V _{I (ON)}	—	V _{CE} = 0.2V, I _C = 5mA	1.2	—	2.4	V
Input voltage (OFF)	V _{I (OFF)}	—	V _{CE} = 5V, I _C = 0.1mA	1.0	—	1.5	V
Transition frequency	f _T	—	V _{CE} = 10V, I _C = 5mA	—	250	—	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = 50V, I _E = 0	—	3	6	pF

Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	—	7	10	13	kΩ
Resistor ratio	R1/R2	—	—	0.9	1.0	1.1	—

